



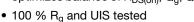
# N-Channel 125 V (D-S) MOSFET



PRODUCT SUMMARY					
V <sub>DS</sub> (V)	125				
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = 10 \text{ V}$	0.0298				
Q <sub>g</sub> typ. (nC)	8				
I <sub>D</sub> (A)	31 <sup>a</sup>				
Configuration	Single				

#### **FEATURES**

 TrenchFET<sup>®</sup> with ThunderFET technology optimizes balance of R<sub>DS(on)</sub>, Q<sub>g</sub>, Q<sub>sw</sub>, and Q<sub>oss</sub>

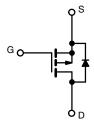


 Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



#### **APPLICATIONS**

- · Primary side switching
- Synchronous rectification
- DC/DC converter
- Motor drive control
- · Load switch



P-Channel MOSFET

ORDERING INFORMATION	
Package	PowerPAK 1212-8S
Lead (Pb)-free and halogen-free	SiSS70DN-T1-GE3

PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		$V_{DS}$	125	V	
Gate-source voltage		$V_{GS}$	± 20	v	
	T <sub>C</sub> = 25 °C		31		
Continuous drain current (T <sub>J</sub> = 150 °C)	T <sub>C</sub> = 70 °C	1 , [	24.8		
	T <sub>A</sub> = 25 °C	† I <sub>D</sub> †	8.5 <sup>b, c</sup>		
	T <sub>A</sub> = 70 °C	1	6.8 <sup>b, c</sup>		
Pulsed drain current (t = 100 μs)		I <sub>DM</sub>	50	A	
	T <sub>C</sub> = 25 °C	,	54.8		
Continuous source-drain diode current	T <sub>A</sub> = 25 °C	ls l	4.2 <sup>b, c</sup>		
Single pulse avalanche current		I <sub>AS</sub>	20		
Single pulse avalanche energy L = 0.1 mH		E <sub>AS</sub>	20	mJ	
	T <sub>C</sub> = 25 °C		65.8		
	T <sub>C</sub> = 70 °C	1 _ [	42.1	W	
Maximum power dissipation	T <sub>A</sub> = 25 °C	P <sub>D</sub>	5.1 <sup>b, c</sup>		
	T <sub>A</sub> = 70 °C	† †	3.2 b, c		
Operating junction and storage temperature range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +150		
Soldering recommendations (peak temperature) c			260	°C	

THERMAL RESISTANCE RAT	NGS				
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum junction-to-ambient <sup>b</sup>	t ≤ 10 s	$R_{thJA}$	20	25	°C/W
Maximum junction-to-case (drain)	Steady state	$R_{thJC}$	1.5	1.9	C/VV

#### Notes

- a.  $T_C = 25 \, ^{\circ}C$
- b. Surface mounted on 1" x 1" FR4 board
- c. t = 10 s
- d. See solder profile (<u>www.vishay.com/doc?73257</u>). The PowerPAK 1212-8S is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components
- f. Maximum under steady state conditions is 65 °C/W

# Vishay Siliconix

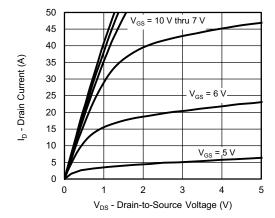
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static					•	ı
Drain-source breakdown voltage	$V_{DS}$	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	125	-	-	V
V <sub>DS</sub> temperature coefficient	$\Delta V_{DS}/T_{J}$	I <sub>D</sub> = 250 mA	-	92	-	
V <sub>GS(th)</sub> temperature coefficient	$\Delta V_{GS(th)}/T_J$	I <sub>D</sub> = 250 μA	-	-7.1	-	mV/°C
Gate-source threshold voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$	2.5	-	4.5	V
Gate-source leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	100	nA
Zono del college delle const		V <sub>DS</sub> = 125 V, V <sub>GS</sub> = 0 V	-	-	1	^
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> = 125 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 70 °C	-	-	15	μA
On-state drain current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \le 10 \text{ V}, V_{GS} = 10 \text{ V}$	20	-	-	Α
Drain-source on-state resistance <sup>a</sup>	R <sub>DS(on)</sub>	$V_{GS} = 10 \text{ V}, I_D = 8.5 \text{ A}$	-	0.0248	0.0298	Ω
Forward transconductance <sup>a</sup>	9 <sub>fs</sub>	$V_{DS} = 15 \text{ V}, I_D = 8.5 \text{ A}$	-	16	-	S
Dynamic <sup>b</sup>	'				•	ı
Input capacitance	C <sub>iss</sub>		-	535	-	pF
Output capacitance	C <sub>oss</sub>	$V_{DS} = 62.5 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	-	157	-	
Reverse transfer capacitance	C <sub>rss</sub>		-	8	-	
<del>-</del>		V <sub>DS</sub> = 62.5 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 8.5 A	-	10.2	15.3	
Total gate charge	$Q_g$		-	8	12	
Gate-source charge	$Q_{gs}$	$V_{DS} = 62.5 \text{ V}, V_{GS} = 7.5 \text{ V}, I_{D} = 8.5 \text{ A}$	-	3.2	-	nC
Gate-drain charge	$Q_{gd}$		-	2.7	-	
Output charge	Q <sub>oss</sub>	V <sub>DS</sub> = 62.5 V, V <sub>GS</sub> = 0 V	-	26	39	
Gate resistance	$R_q$	f = 1 MHz	0.24	1.2	2.4	Ω
Turn-on delay time	t <sub>d(on)</sub>		-	20	40	
Rise time	t <sub>r</sub>	$V_{DD} = 62.5 \text{ V}, R_L = 9.2 \Omega, I_D \cong 6.8 \text{ A},$	-	9	18	
Turn-off delay time	t <sub>d(off)</sub>	$V_{GEN}$ = 10 V, $R_g$ = 1 $\Omega$	-	30	60	
Fall time	t <sub>f</sub>			10	20	
Turn-on delay time	t <sub>d(on)</sub>		-	22	44	ns
Rise time	t <sub>r</sub>	$V_{DD} = 62.5 \text{ V}, R_L = 9.2 \Omega, I_D \cong 6.8 \text{ A},$	-	12	24	
Turn-off delay time	t <sub>d(off)</sub>	$V_{GEN} = 7.5 \text{ V}, R_g = 1 \Omega$	-	30	60	
Fall time	t <sub>f</sub>		-	12	24	
<b>Drain-Source Body Diode Characteristi</b>	cs		•		•	•
Continuous source-drain diode current	I <sub>S</sub>	T <sub>C</sub> = 25 °C	-	-	54.8	
Pulse diode forward current	I <sub>SM</sub>		-	-	50	Α
Body diode voltage	$V_{SD}$	$I_S = 6.8 \text{ A}, V_{GS} = 0 \text{ V}$	-	0.8	1.2	V
Body diode reverse recovery time	t <sub>rr</sub>		-	46	92	ns
Body diode reverse recovery charge	Q <sub>rr</sub>	$I_F = 6.8 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s},$	-	82	164	nC
Reverse recovery fall time	t <sub>a</sub>			37	-	
Reverse recovery rise time	t <sub>b</sub>		-	9	_	ns

#### Notes

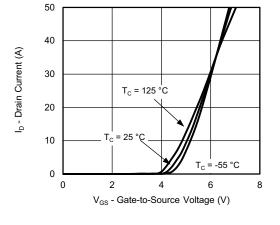
- a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %
- b. Guaranteed by design, not subject to production testing

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

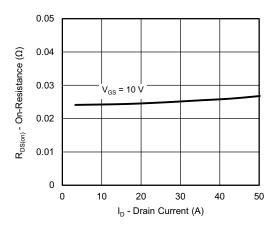




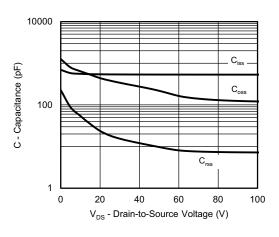
#### **Output Characteristics**



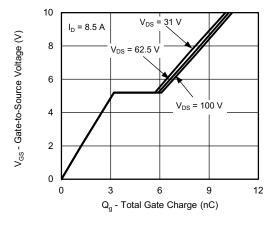
**Transfer Characteristics** 



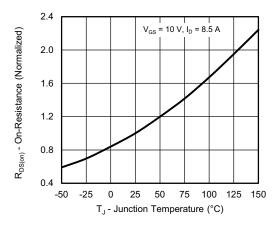
On-Resistance vs. Drain Current and Gate Voltage



Capacitance

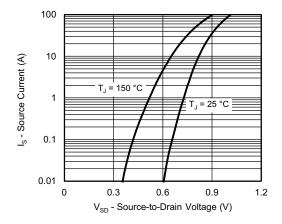


**Gate Charge** 

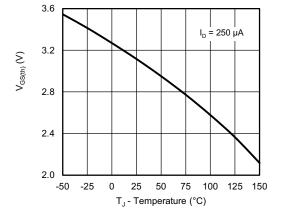


On-Resistance vs. Junction Temperature

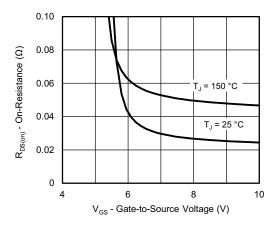




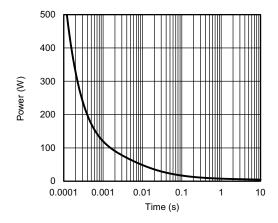
Source-Drain Diode Forward Voltage



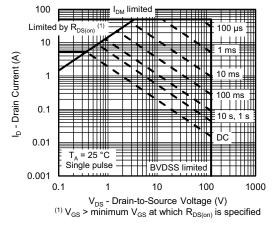
Threshold Voltage



On-Resistance vs. Gate-to-Source Voltage

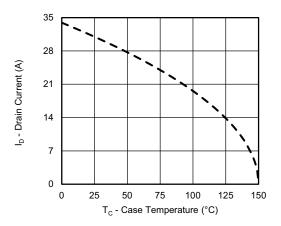


Single Pulse Power, Junction-to-Ambient

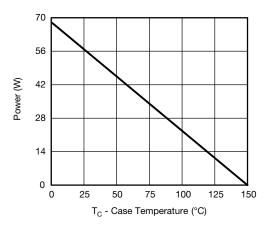


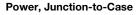
Safe Operating Area, Junction-to-Ambient

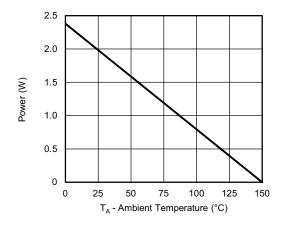




### Current Derating a





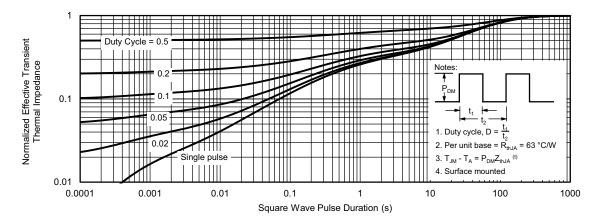


Power, Junction-to-Ambient

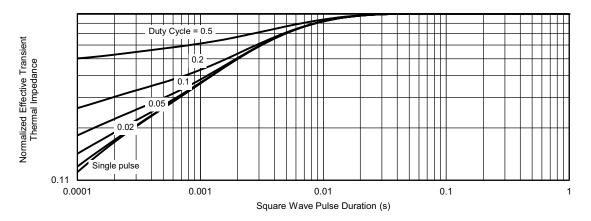
#### Note

a. The power dissipation P<sub>D</sub> is based on T<sub>J</sub> max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit





Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

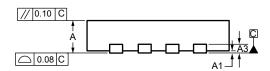
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# Case Outline for PowerPAK® 1212-8S





DIM.	MILLIMETERS			INCHES			
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
Α	0.67	0.75	0.83	0.026	0.030	0.033	
A1	0.00	-	0.05	0.000	-	0.002	
A3		0.20 ref.			0.008 ref		
b	0.25	0.30	0.35	0.010	0.012	0.014	
D	3.20	3.30	3.40	0.126	0.130	0.134	
D1	2.15	2.25	2.35	0.085	0.089	0.093	
E	3.20	3.30	3.40	0.126	0.130	0.134	
E1	1.60	1.70	1.80	0.063	0.067	0.071	
е		0.65 bsc.			0.026 bsc.		
K		0.76 ref.			0.030 ref.		
K1	0.41 ref.			0.016 ref.			
L	0.33	0.43	0.53	0.013	0.017	0.021	
Z	0.525 ref.			0.021 ref.			

ECN: C20-0862-Rev. B, 20-Jul-2020

DWG: 6008



## RECOMMENDED MINIMUM PADS FOR PowerPAK® 1212-8 Single



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE



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